

IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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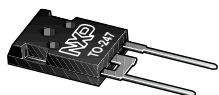
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Thank you for your cooperation and understanding,

WeEn Semiconductors



BYC30W-600P

Hyperfast power diode

10 February 2014

Product data sheet

1. General description

Hyperfast power diode in a SOD142 (2-lead TO247) plastic package.

2. Features and benefits

- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_{mb} \leq 115\text{ }^{\circ}\text{C}$; square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	30	A
Static characteristics						
V_F	forward voltage	$I_F = 30\text{ A}$; $T_j = 150\text{ }^{\circ}\text{C}$; Fig. 6	-	1.38	1.8	V
Dynamic characteristics						
t_{rr}	reverse recovery time	$I_F = 1\text{ A}$; $V_R = 30\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	18	22	ns

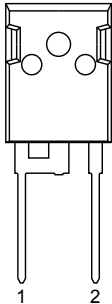
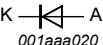


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 TO-247 (SOD142)	
2	A	anode		
mb	mb	mounting base; connected to cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC30W-600P	TO-247	Plastic Single-ended through-hole package; Heatsink mounted; 1 mounting hole; 2-lead TO-247	SOD142

7. Marking

Table 4. Marking codes

Type number	Marking code
BYC30W-600P	BYC30W-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_{mb} \leq 115\text{ }^{\circ}\text{C}$; square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3	-	30	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25\text{ }\mu\text{s}$; $T_{mb} \leq 115\text{ }^{\circ}\text{C}$; square-wave pulse	-	60	A

Symbol	Parameter	Conditions		Min	Max	Unit
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; Fig. 4		-	270	A
		t _p = 8.3 ms; T _{j(init)} = 25 °C; sine-wave pulse; Fig. 4		-	300	A
T _{stg}	storage temperature			-65	175	°C
T _j	junction temperature			-	175	°C

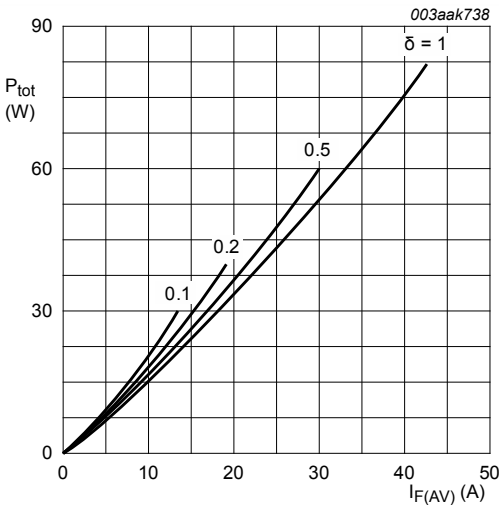


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$
$$V_O = 1.798 \text{ V}; R_S = 0.003 \text{ }\Omega$$

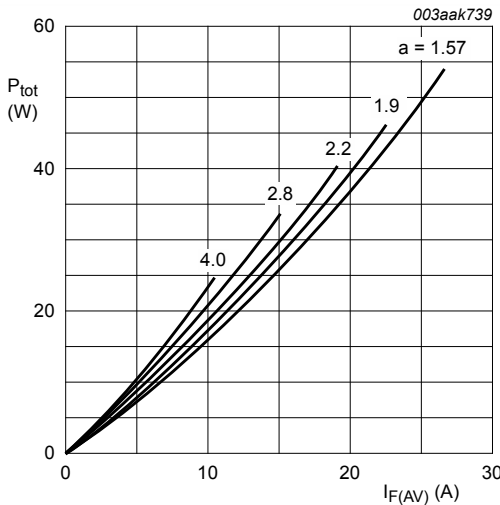


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$
$$V_O = 1.798 \text{ V}; R_S = 0.003 \text{ }\Omega$$

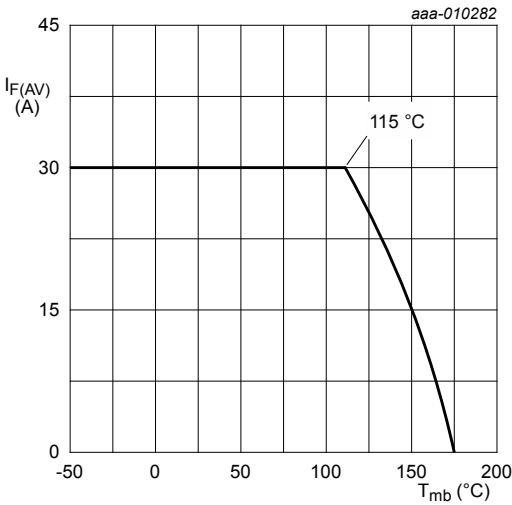


Fig. 3. Forward current as a function of mounting base temperature; maximum values

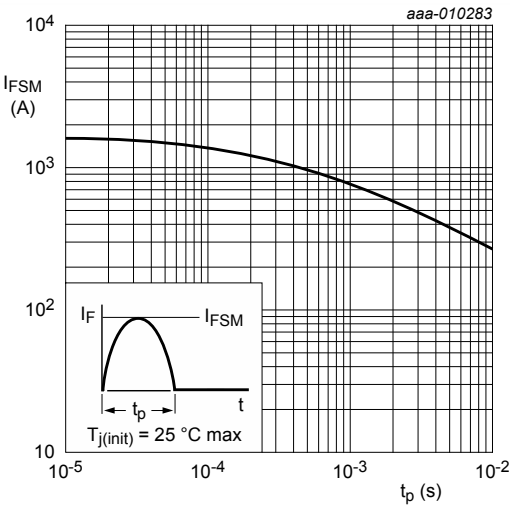


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	45	-	K/W

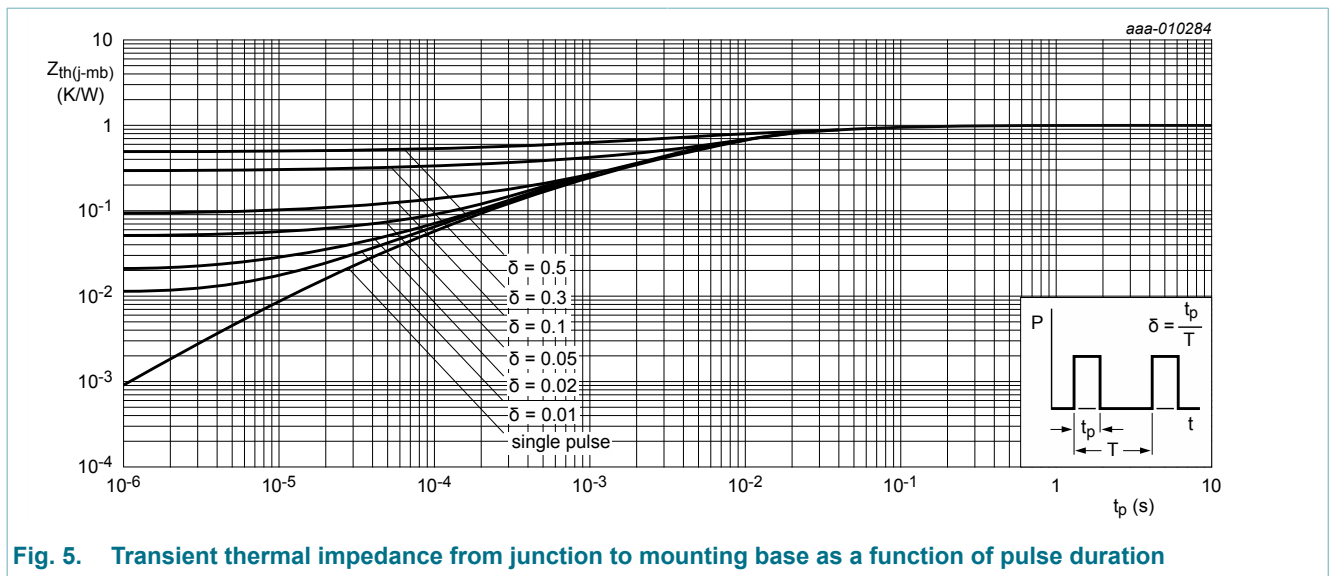


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; Fig. 6		-	2	2.75	V
		I _F = 30 A; T _j = 150 °C; Fig. 6		-	1.38	1.8	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C		-	-	10	μA
		V _R = 600 V; T _j = 150 °C		-	-	1	mA
Dynamic characteristics							
Q _r	recovered charge	I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 25 °C; Fig. 7		-	50	-	nC
		I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; Fig. 7		-	280	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{rr}	reverse recovery time	$I_F = 1\text{ A}$; $V_R = 30\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	18	22	ns
		$I_F = 30\text{ A}$; $V_R = 200\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	35	-	ns
		$I_F = 30\text{ A}$; $V_R = 200\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ }^\circ\text{C}$; Fig. 7	-	70	-	ns
		$I_F = 30\text{ A}$; $V_R = 400\text{ V}$; $dI_F/dt = 500\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	29	-	ns
I_{RM}	peak reverse recovery current	$I_F = 30\text{ A}$; $V_R = 200\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	3.5	-	A
		$I_F = 30\text{ A}$; $V_R = 200\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ }^\circ\text{C}$; Fig. 7	-	7.6	-	A

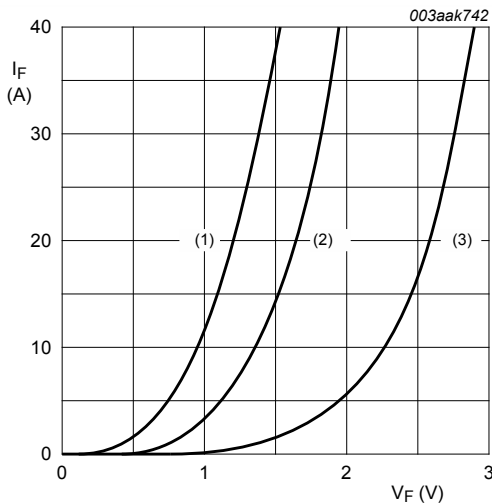


Fig. 6. Forward current as a function of forward voltage

- (1) $T_j = 150\text{ }^\circ\text{C}$; typical values;
(2) $T_j = 150\text{ }^\circ\text{C}$; maximum values;
(3) $T_j = 25\text{ }^\circ\text{C}$; maximum values;
 $V_O = 1.798\text{ V}$; $R_S = 0.003\text{ }\Omega$

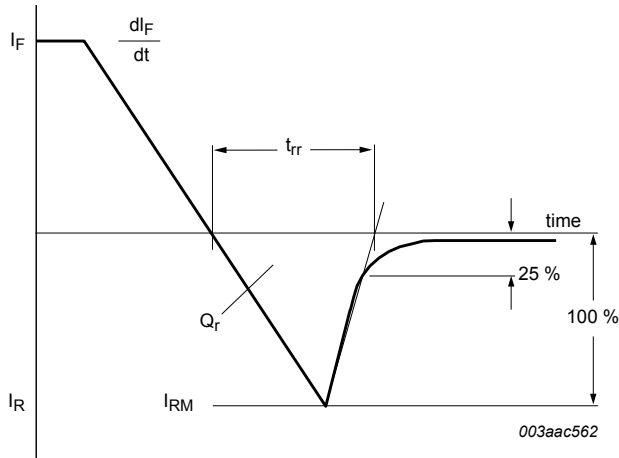


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline

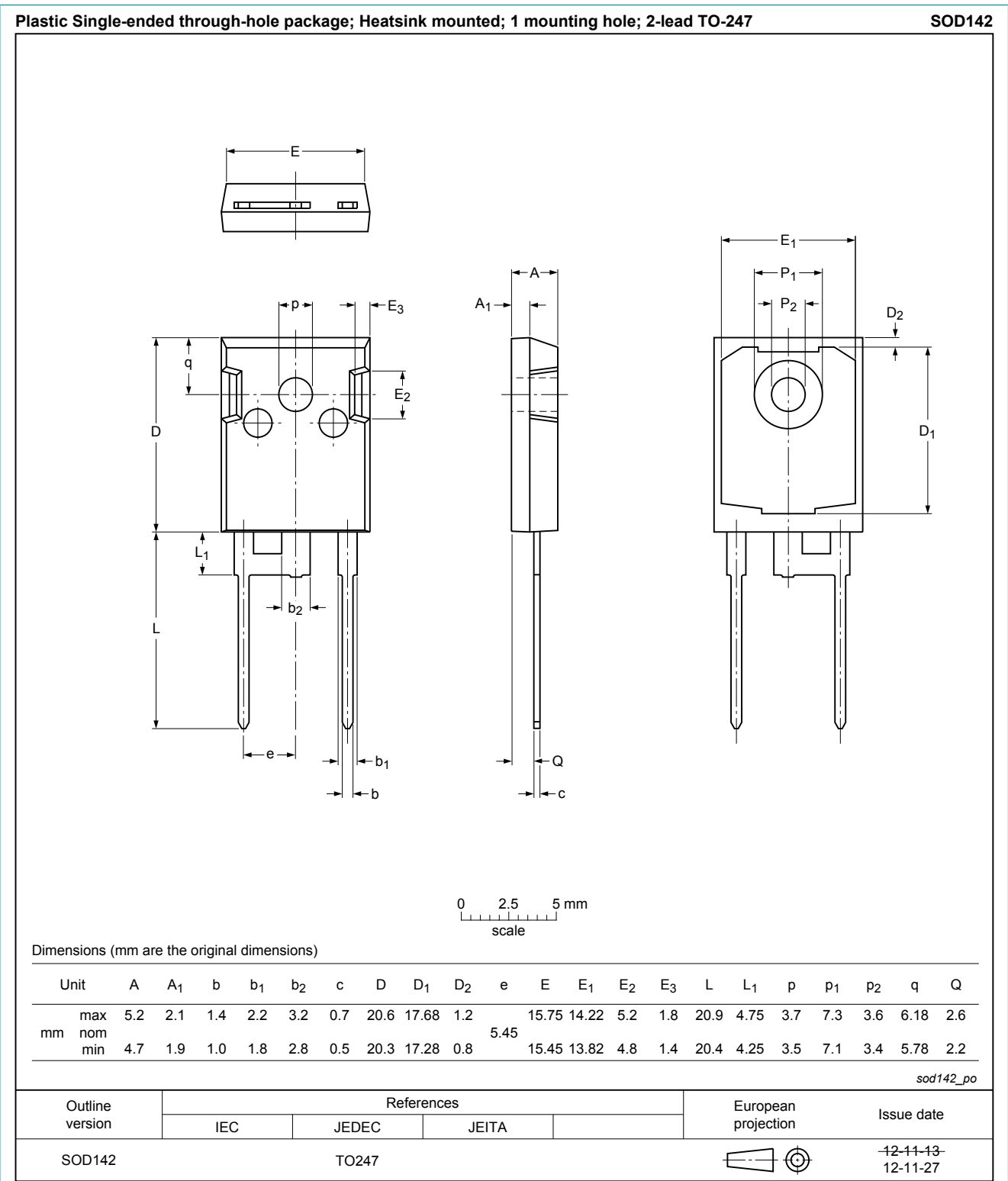


Fig. 8. Package outline TO-247 (SOD142)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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